

### AMENDMENTS TO THE CLAIMS

Kindly amend claims 1, and 11-14, and cancel claims 10, 17-22 and 25 as shown in the listing of claims below. This listing of claims will replace all prior versions, and listings of claims in the application.

### LISTING OF CLAIMS

1 Claim 1. (currently amended) A method for a controlled release of structures comprising:

- 2 a) forming one or more trenches in a layer of device material;
- 3 b) filling one or more selected trenches with an etch-stop material to form one or more
- 4 etch-stop trenches;
- 5 c) defining one or more structures between the selected trenches;
- 6 d) forming a structural layer proximate one or more exposed areas of the device layer;
- 7 and
- 8 ~~[[d)]~~ e) etching one or more portions of the device layer between the etch-stop trenches to
- 9 release the structures, wherein the etching does not etch the etch-stop material.

1 Claim 2. (original) The method of claim 1, wherein b) includes depositing etch-stop material

2 over the surface of the device layer.

1 Claim 3. (original) The method of claim 2 wherein c) includes forming one or more openings

2 in the etch-stop material that has been deposited over the surface of the device layer.

1 Claim 4. (original) The method of claim 2, wherein the etching undercuts one or more portions

2 of the etch-stop material that has been deposited over the surface of the device layer.

1 Claim 5. (original) The method of claim 1 where the layer of device material is disposed

2 between two layers of etch-stop material.

1 Claim 6. (original) The method of claim 1, wherein the device layer includes one or more

2 layers of a silicon-on-insulator (SOI) substrate.

1 Claim 7. (original) The method of claim 1, wherein the device layer is a layer of glass, quartz

2 or oxide.

1 Claim 8. (original) The method of claim 1, wherein d) includes a wet etch process.

1 Claim 9. (original) The method of claim 1, wherein d) includes a dry etch process.

1 Claim 10. (cancel)

1 Claim 11. (currently amended) The method of claim [[10]] 1, wherein the etch process in d)  
2 does not etch the structural layer.

1 Claim 12. (currently amended) The method of claim [[10]] 1, further comprising releasing one  
2 or more portions of the structural layer.

1 Claim 13. (currently amended) The method of claim [[10]] 1, wherein the etch process in d)  
2 releases one or more portions of the structural layer.

1 Claim 14. (currently amended) The method of claim [[10]] 1, wherein the structural layer  
2 includes one or more structures that are formed directly on top of [[the]] an etch-stop layer.

1 Claim 15. (original) The method of claim 14, wherein the structural layer contains two or more  
2 sub-layers.

1 Claim 16. (previously presented) A process for forming structures comprising:

- 2 i) forming one or more trenches in a layer of device material;  
3 ii) filling one or more selected trenches with an etch-stop material to form one or more etch-  
4 stop trenches;  
5 iii) masking a surface of the layer of device material to expose one or more selected areas of  
6 device material that border one or more of the etch-stop trenches; and  
7 iv) forming one or more structures on one or more of the selected areas of the device  
8 material that were exposed; and  
9 v) etching one or more of the selected areas of the device layer to release the structures,  
10 wherein the etching does not etch the etch-stop material.

1 Claim 17. (cancel)

1 Claim 18. (cancel)

1 Claim 19. (cancel)

1 Claim 20. (cancel)

1 Claim 21. (cancel)

1 Claim 22. (cancel)

1 Claim 23. (currently amended) The method of claim [[10]] 1, wherein the structural layer is  
2 protected by one or more etch-stop layers.

1 Claim 24. (previously presented) The method of claim 16, wherein one or more of the structures  
2 include a device layer protected by one or more etch-stop layers.

1 Claim 25. (cancel)